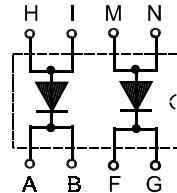


# Fast Recovery Epitaxial Diode (FRED)

## DSEI 2x61

$I_{FAVM} = 2 \times 60 \text{ A}$   
 $V_{RRM} = 1000 \text{ V}$   
 $t_{rr} = 35 \text{ ns}$

$V_{RSM}$	$V_{RRM}$	Type
V	V	
1000	1000	DSEI 2x 61-10P



Symbol	Conditions	Maximum Ratings (per diode)		
$I_{FRMS}$	$T_{VJ} = T_{VJM}$	100	A	
$I_{FAVM}$ ①	$T_C = 50^\circ\text{C}$ ; rectangular; $d = 0.5$	60	A	
$I_{FRM}$	$t_p < 10 \mu\text{s}$ ; rep. rating; pulse width limited by $T_{VJM}$	800	A	
$I_{FSM}$	$T_{VJ} = 45^\circ\text{C}$ ; $t = 10 \text{ ms}$ (50 Hz), sine	500	A	
$T_{VJ}$		-40...+150	°C	
$T_{VJM}$		150	°C	
$T_{stg}$		-40...+150	°C	
$P_{tot}$	$T_C = 25^\circ\text{C}$	180	W	
$V_{ISOL}$	50/60 Hz, RMS $t = 1 \text{ min}$	2500	V~	
	$I_{ISOL} \leq 1 \text{ mA}$ $t = 1 \text{ s}$	3000	V~	
$M_d$	Mounting torque (M4)	1.5 - 2.0 14 - 18	Nm lb.in.	
<b>Weight</b>		18	g	

Symbol	Conditions	Characteristic Values (per diode)		
		typ.	max.	
$I_R$	$T_{VJ} = 25^\circ\text{C}$ $V_R = V_{RRM}$ $T_{VJ} = 25^\circ\text{C}$ $V_R = 0.8 \cdot V_{RRM}$ $T_{VJ} = 125^\circ\text{C}$ $V_R = 0.8 \cdot V_{RRM}$	3 0.5 14	mA mA mA	
$V_F$	$I_F = 60 \text{ A}$ ; $T_{VJ} = 150^\circ\text{C}$ $T_{VJ} = 25^\circ\text{C}$	1.8 2.3	V V	
$V_{T0}$	For power-loss calculations only	1.65	V	
$r_T$	$T_{VJ} = T_{VJM}$	8.3	$\text{m}\Omega$	
$R_{thJC}$		0.7	K/W	
$R_{thCK}$		0.05	K/W	
$t_{rr}$	$I_F = 1 \text{ A}$ ; $-\text{di}/\text{dt} = 200 \text{ A}/\mu\text{s}$ $V_R = 30 \text{ V}$ ; $T_{VJ} = 25^\circ\text{C}$	35	50	ns
$I_{RM}$	$V_R = 540 \text{ V}$ ; $I_F = 60 \text{ A}$ ; $-\text{di}_F/\text{dt} = 480 \text{ A}/\mu\text{s}$ $L \leq 0.05 \mu\text{H}$ ; $T_{VJ} = 100^\circ\text{C}$	32	36	A
$d_s$	Creeping distance on surface	min. 11.2	mm	
$d_A$	Creeping distance in air	min. 11.2	mm	
$a$	Allowable acceleration	max. 50	$\text{m}/\text{s}^2$	

①  $I_{FAVM}$  rating includes reverse blocking losses at  $T_{VJM}$ ,  $V_R = 0.8 V_{RRM}$ , duty cycle  $d = 0.5$   
Data according to IEC 60747

